Seat No.				Set	P
М.	Sc. Phy	ysics (Applied Electronics) (Examination: Marc Mathematical Phys	h/April - 2025	BCS	5)
•		Thursday, 15-May-2025 PM To 05:30 PM	Max. I	Marks	: 60
Instru	ctions:	 All questions are compulsory Figures to the right indicate for 			
Q.1 A	1)	c) The integral of a function ale contour itselfd) The integral of a function ale	b) Exponential d) Division es that: ong a closed contour is zero ong a closed contour is nonzer ong a contour depends on the ong a contour is infinity ssian distribution in the time		08
	4)	 b) Sine function in the frequen c) Cosine function in the frequen d) Delta function in the frequer In the Fourier series representa 	cy domain ency domain ncy domain		
	")	coefficients corresponding to oc a) Zero c) Constant	•		
	5)	The number of arbitrary constant differential equation of second (a) 1 c) 2			
	6)	The non-zero Particular Integra differential equation. a) Homogeneous c) Second order Homogeneou	b) Non-Homogeneous		

		7)	a)	Hilbert spa Anticomr Additivity	•	oroperty (does b) d)	Distrib	ner product outivity ciativity	satisfy?	
		8)	Th a) c)	0	he zero mat	trix?	b) d)	1 The ra	ank is unde	efined	
	B)	wr a) b) c) d)	A sthe The hor Ca poi	e set can be e Wronski mogeneou luchy's Internation	tions is a cope expressed an of a set of its contons of its contons eries expares	d as a lir of solutic with con Ila expre our integ	near one to stant sses ral.	combir a sec coeffice the va	nation of the ond-order cients is alv llue of a fur	e others. ways zero nction at a	
Q.2	Ans a)				g question matrix is un		•	i = [i]	0]		12
	b) c) d)	Fin De	id th fine	ne Norms	of given equ e's theorem	uation $f($	t) =	t+2	1-		
	e)			$4\frac{d^2y}{dx^2} + 4\frac{d^2y}{dx^2}$							
	f) g) h)	De	fine		$and b_n$ in Fo $f(z) = 0$		ies.				
Q.3	Ans	wer	the	e followin	g question	(Any Th	ree)				12
	a)				ection $f(z) =$						
	b) c) d)	De S =	C scri tern = {(1	calculate the Argand hine linear 1, -1, 2), (2	the singular ne residues d Diagram. independe $1, -2, 1), (1, \frac{dy}{dx} + 29y =$	at each once of for 1,4)	of the	e singu	•		
Q.4	Ans a)				g question ntial equation		-	= cos	x		12
	b)				egral $f(z) =$	$ \oint \frac{\sin(z)}{Z^2 + 4} $	dz w	here, <i>C</i>	is the circ	z = 3	

c) Determine whether the following in R³ is linearly independent.

$$\{(1,-2,1),(2,1,1),(7,-4,1)\}$$

Q.5 Answer the following (Any Two)

- a) Find $L(te^{-2t} \sin 2t \sin 3t)$
- **b)** Solve $\frac{d^2y}{dx^2} 10\frac{dy}{dx} + 25y + 0$
- Find the inverse of a matrix $A = \begin{bmatrix} 7 & 2 & 1 \\ 0 & 3 & -1 \\ -3 & 4 & -2 \end{bmatrix}$

Seat No.	Set	P	
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M.Sc. Physics (Applied Electronics) (Semester - I) (New) (NEP CBCS) Examination: March/April - 2025 Solid State Physics (2323102)

				Solid State Phys		-	
•				rday, 17-May-2025 o 05:30 PM		Max. Marks: 6	С
Instr	uctio	ns:		All questions are compulsor Figures to the right indicate		marks.	
Q.1	•		The a)	se correct alternative. Bloch theorem is crucial fo Dielectric properties Superconductivity	b)	Band structure in solids	8
	2	2) ⁻	a) b) c)	Meissner effect demonstra Perfect diamagnetism in so Magnetic susceptibility in f Curie-Weiss behavior in pa None of the above	uper errite	2 S	
	3	3) ⁻	a)	Neel temperature is associ Superconductivity Ferrimagnetism	b)	with Antiferromagnetism Ferroelectricity	
	4	-	clou a)		e to b) d)	the distortion of the electron Orientational Dielectric	
	į	5) ⁻	a) b) c)	Kronig-Penney model explains the energy gap in semicor Susceptibility in magnetic Polarization mechanisms None of the above	nduc	tors	
	•	6) (a)	erconductivity is destroyed Low temperatures Room temperature	b)	High magnetic fields Low pressures	
	7	7)	a)	imagnetic materials are cha Equal and opposite spins Random spin alignment	b)	Unequal opposing spins	

		 a) Magnetic permeability and susceptibility b) Polarizability and dielectric constant c) Electrical conductivity and temperature d) None of the above 	
	B)	 d) None of the above Fill in the blanks: The energy bands in solids arise due to the potentiant. Superconductors exhibit perfect diamagnetism due to the effect. Antiferromagnetic materials have a critical temperature of the The equation is used to calculate the internal field in dielectric. 	alled
Q.2	a) b) c) d) e) f)	Discuss the significance of the Meissner effect in superconductor. What is the Curie point? Explain the electronic polarization in dielectrics. Write about the energy gap in semiconductors. Differentiate between Type I and Type II superconductors. Classify the magnetic materials.	12 ors.
Q.3	Ans a) b) c) d)	wer the following (Any Three). Derive the London equations in superconductivity. Describe the electrical conductivity in metals. Write about the Langevin theory of paramagnetism. Discuss the Brillouin zones.	12
Q.4	Ans a) b) c)	wer the following (Any Two). Derive the Clausius-Mossotti equation. Explain the dipole theory of ferroelectricity. Write a note on saturation magnetization and its temperature dependence.	12
Q.5	Ans a) b) c)	wer the following (Any Two). Describe the Josephson effect and its applications. Discuss the thermodynamics of superconductors. Write a detailed note on ferrimagnetic materials.	12

The Clausius-Mossotti equation relates

8)

Seat No.						Set	P			
М.	M.Sc. Physics (Applied Electronics) (Semester - I) (New) (NEP CBCS) Examination: March/April - 2025 Analog and Digital Electronics (2323106)									
•	Day & Date: Monday, 19-May-2025 Max. Marks: 60 Time: 03:00 AM To 05:30 PM									
Instru	ctic	ns:	•	ons are compulsory o the right indicate f		arks.				
Q.1 A	A)		If a signal p			inhibited by sending a LOW at is HIGH, the gate is a(n): NAND OR	80			
		2)	a) It has anb) It has inc) It contain	e following is true an internal memory terfacing circuits ns ALU, CU, and retarvard architecture	egiste					
		3)		l serial load and int		ept a parallel input, or a shift features, called? end around conversion				
		4)	The output HIGH when a) A = 1, B = c) A=1, B=	=1, C=0	b)	e inputs. A, B, and C, is A=0, B=0, C=0 A=1, B=0, C=1				
		5)	a) infinite of	erational amplifier houtput impedance bandwidth	b)	zero input impedance All of the above				
		6)	A series dis a) linear re c) shunt re	gulator		example of a switching regulator dc-to-dc converter				
		7)	a) all input	of a NOR gate is H s are HIGH ut is LOW		any input is HIGH				

		8)	in	hich of the following logical Boolean algebra? inversion OR	operat b) d)	ions is represented by the + sigr AND Complementation	1
	B)	Fill 1) 2) 3) 4)	Th Op A i lea	o-amp circuits are used in _ microprocessor with the ned ast two memory ICs: ROM o	e buffe v essar r EPR	er is with the input voltage	
Q.2	Anso a) b) c) d) e) f) g) h)	Der Wh Der Wh	fine nat i fine nat i fine nat i	e following. (Any Six) the term common mode reare the operations performed is instrumentation amplifier. It is slew rate. It is linear that the voltage regulator. It is opcode fetch cycle. It is differential gain related to a	d by A	n ratio. ALU of 8085.	12
Q.3	Ansv a) b) c) d)	Dra Lis	aw 1 t th scri	e following. (Any Three) the circuit diagram of an Op e Software and Hardware ir ibe some of the characterist the logic diagram of SR flip	iterrup	based Wein bridge oscillator? ets of 8085? practical Op-amp?	12
Q.4	Ansva) b)	Wheregon	nat i gula aw t nfig ite a	e following. (Any Two) is switching regulator? Wha tor? Explain them in details the circuit of summing ampl uration. an equation for the output v n briefly about bus structure	with sifier us	ne types of switching uitable figure? sing inverting amplifier for this circuit	12
Q.5	Ansv a) b) c)	What to	nat i the aw a	output from a Sine-wave? and explain the architecture	of 808	d to produce a square -wave	12

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Seat	Sat	D
No.	Set	

M.Sc. Physics (Applied Electronics) (Semester - I) (New) (NEP CBCS) Examination: March/April - 2025 Research Methodology in Physics (2323105)

	researon methodology in		y 3103 (2020 100)
-	Saturday, 24-May-2025 PM To 05:30 PM		Max. Marks: 60
Instructions	2) Figures to the right indicate ful	l ma	arks.
•	The main problem in questionnaing a) Accessible to Diverse Responsible to Greater Anonymity c) Shows an inability of responsible to None of these	nde	ent
2)	UV-V is spectroscopy cannot ana a) don't interact c) merge	b)	e compounds that with light. interact none of the above
3)	By selecting laser operating cond is a) possible c) not defined	b)	impossible both a) and b)
4)	In DC sputtering, bias is apartive c) No	b)	ed to the target material. Positive All of the above
5)	Resistive thermal deposition can points. a) boiling c) melting	b)	osit materials with low decimal none of the above
6)	HRTEM provides images. a) medium resolution c) low resolution	b) d)	poor resolution high resolution
7)	Qualitative methods are probably techniques, the method of Qualita a) Questionnaire c) Depth Interview	ative b)	
8)	Electronic interview can be condu a) Telephonic c) Personal		Fax

	в)	In PLD, kinetic energies of ablated particles are high enough to promote surface diffusion. (True/False) In thermal evaporation, films in the thickness range of angstroms to microns are obtained. (True/False) 3) sampling is a probability sampling method. 4) In sputtering, magnets behind cathode trap electrons.	04
Q.2	Ans a) b) c) d) e) f) g)	What are the applications of UV-Vis Spectroscopy? State the physical conditions of DC and RF sputtering. Define Quantitative research method. State the various tools for data analysis. Draw the neat labeled diagram of electrodeposition method. What are the applications of FTIR Spectroscopy. Enlist the Data Processing strategies. Write the applications of Pulsed Laser Deposition.	12
Q.3	Ans a) b) c) d)	Write a note on Patents. Draw the neat labeled diagram of HRTEM instrument. Define physical and chemical vapour deposition. Write a note on Applied Vs. Fundamental research methods.	12
Q.4	a)	Explain different techniques and methods of good sampling. Write in detail about the concept of Chemical Bath Deposition. Write in detail about the construction and working of SEM.	12
Q.5	Ans a) b) c)	Write a note on Review of Literature. What is Research Methodology? What are the requisites for Good Scientific Research? Explain the construction and working of Fourier Transform Infrared Spectroscopy.	12

Seat No.					Set F)				
М.\$	M.Sc. Physics (Applied Electronics) (Semester - II) (New) (NEP CBCS) Examination: March/April - 2025 Quantum Mechanics (2323201)									
Day & Date: Wednesday, 14-May-2025 Time: 11:00 AM To 01:30 PM Max. Marks:										
Instru	ıctioı		 All questions are compulsor Figures to right indicate full 	-	S.					
Q.1 /	•	1) F	ose correct alternative. Raising operator is defined as a) $L_x + iL_y$ c) $iL_z - iL_y$	b)		8				
	4	V	Momentum of particle by de-Browvelength. a) inversely proportional c) in phase	b)						
	3	į	Potential energy of a particle in $=$ $=$ $=$ $=$ $=$ $=$ $=$ $=$ $=$ $=$		nonic oscillator having mass m $(1/2)m\omega^2x^2$ $(1/2)mv^2$					
	4	t	f Ψ_a and Ψ_b are said to be orth he following is true. a) $\langle \Psi_a \Psi_b \rangle = 1$ c) $\langle \Psi_a \Psi_b \rangle = \sqrt{1/2}$	b)	al to each other, then which of $\langle \Psi_a \Psi_b \rangle = \infty$ $\langle \Psi_a \Psi_b \rangle = 0$					
	5		「he commutation relation betw a) <i>iћ</i> , 0 c) <i>ーiћ</i> , 1	veen [: b) d)	0, <i>iħ</i>					
	6		The eigen value of L^2 is a) $l(l+1)\hbar^2$ c) $l(l^2+1)\hbar^2$	b)	$l(l-1)\hbar \ l(l+1)\hbar$					
	7	b	The minimum energy of particle box is by substituting n equal to a) one c) half		ined to one dimensional rigid zero two					
	8	3) T	The eigen value of spin matrice ± 2 c) ± 1	,						

	B)	 Fill in the blanks OR write true/false. Inner product of bra and ket in Quantum Mechanics is always 1. (True/False) Probability density is always positive. (True/False) For a free particle the potential energy V(x) = The linear momentum operator is given by 	04
Q.2	a) b) c) d) e) f)	Define Hamiltonian operator. Write about the energy of harmonic oscillator. What is the probability density? Define the orthogonality and normalization. Write in short about the Dirac delta function. What is Compton effect? What is meant by rigid box? What is a complex function? Give an example.	12
Q.3	a) b) c)		12 ′).
Q.4	Ans a) b) c)	What is Schrodinger wave equation? Write in detail about Schrodinger time independent wave equation.	12
Q.5	Ans a) b) c)	Obtain eigen values of operators L^2 and Lz . Describe the Pauli spin matrices. Explain i) Schartz's Inequality ii) State vector iii) Span iv) Basis	12

Seat	Sat	D
No.	Set	

M.Sc. Physics (Applied Electronics) (Semester - II) (New) (NEP CBCS)

		•	Examination: Ma Electrodynami		-
•			Friday, 16-May-2025 AM To 01:30 PM		Max. Marks: 60
Insti	ructio	ons:	 All questions are compulso Figures to the right indicate 	-	narks.
Q.1	A)	_	oose correct alternative. The electrostatic energy in ar of the following?	ı elect	08 ric field does not depend on which
			a) Magnitude of chargesc) Applied electric field	b) d)	Permittivity Flux lines
		2)	If the electric potential is give calculated? a) Electrostatic energy	b)	Electric field intensity
			c) Electric flux density	d)	Permittivity
		3)	Electric field intensity is a a) Scalar c) Both (a) and (b)	b)	quantity. Vector None of the above
		4)	The skin effect is a phenome a) Insulators c) Conductors		Dielectrics
		5)	Lorentz electric force has directly a) Similar to electric field c) Scalar quantity	_	
		6)	Electric intensity at any point point. a) Electric flux c) Potential gradient	in an e b) d)	•
		7)	The Biot-Savart's law is a ger a) Kirchhoff's law c) Ampere's law		Lenz's law
		8)	The skin depth is used to find a) DC resistance c) Permittivity	b)	n parameter? AC resistance Potential

SLR-ZQ-7

	B)	 Write True/False. The work done in moving a test charge from one point to another in an equipotential surface is zero. When curl of a path is zero, the field is said to be conservative. In static magnetic field only magnetic dipole exist. The magnetic field intensity will be zero inside a conductor. 	04
Q.2	Ans a) b) c) d) e) f) g) h)	wer the following. (Any Six) State Biot-Savart law. Explain the electromagnetic force. How electromagnetism works? Define Poynting vector. What is an electric field? Write Maxwell equation derived from Faradays law. What is an electromagnetic wave? Define Skin effect.	12
Q.3	Ans a) b) c) d)	wer the following. (Any Three) Explain differential form of Ampere's law. Explain energy stored in electric field. State the boundary condition for an electrostatic field Ē. Explain Maxwell displacement current.	12
Q.4	Ans a) b) c)	wer the following. (Any Two) What is gauss law? Explain differential form of its. Discuss electromagnetic plane waves in stationary medium. Explain the concept of Thomson cross section.	12
Q.5	Ans a) b) c)	wer the following. (Any Two) Explain boundary condition between conductor and free space. State and prove Poynting theorem. Explain in short radiation from a half wave antenna.	12

Seat No.								Set	Р
М.	Sc. P	hysic	E	xaminatio	n: Marc	h/A	ester - II) (New pril - 2025 22323206)) (NEP CBCS	i)
			sday, 20- To 01:30	May-2025 PM				Max. Marks	: 60
Instr	uctio	-	-	ions are co o the right i			arks.		
Q.1	A)	1) _ a) c) 2) T a) b) c)	Holonor Scleron The phase Position Momen Both Po	mic	nts are ir ers to es nates	b) d)			08
		a)	Vhich is t nechanics F=m/a F=m+a		natical sta	b) d)	ent of 2 nd law of l F=ma F=m-a	Newtonian	
		,	<pre> fo</pre>	r circular or	bit the va	b)	of eccentricity. $\in < 1$ $\in = 0$		
		'a)	Invariar		tion are _	b)	under Galilean tr Variant changes its sigr		
		a)	Degrees o 0 3	f freedom f	or fly who	eel _ b) d)	1		
		a)	Vhich of t [X,Y]= [[X, Y]=	Y,X]	g is true f	b)	oisson bracket? [X,Y]=2[Y,X] [X,X]=[Y,Y]=1		
		a)	he gener Identity Zero	ating functi	on F1(q,	Q,t) (b) d)	generates Exchange Infinite	transformat	ion.

	B)	 Fill in the blank OR true /False. The motion of the planets around the sun is the example of the motion under central force field. (True/False) In Lagrange's equation, the motion of the system has been described by force. (True/False) The equation of Jacobi's Identity is As per Kepler's third law of planetary motion, square of a time period is directly proportional to cube of a 	04
Q.2		wer the following. (Any Six)	12
	-	Define central force and give its characteristics? How to analyse the orbits?	
	c)	What is the Jacobi integral?	
	-	Define the conservation of linear and angular momenta.	
	-	Write in short about the open system. What is Euler-Lagrangian differential equation?	
		Write the condition for transformation to be canonical.	
		What is the constant of motion?	
\cap 2	۸nc	war the following (Any Three)	12
Q.3		wer the following. (Any Three) Give an account about conservation of energy in case of mechanics	12
	,	of particles.	
	b)	What are constraints? Explain in detail about their types with suitable	
	c)	examples. Check whether the transformation defined as Q=1/p, P=qp ² is	
	c,	canonical or not.	
	d)	State Hamilton's variational principle and derive the Lagrange's	
		equation of motion form it?	
Q.4	Ans	wer the following. (Any Two)	12
	a)	Explain	
		Gauge invariance of Lagrangian equation	
	b)	 Gyroscopic forces Explain and prove the principle of least action. 	
	c)	Derive an equivalent equation for reduction to one body problem from	
	,	two body problem.	
Q.5	Λne	wer the following. (Any Two)	12
Q. J	a)	Elaborate the differences between Classical Mechanics and	12
	,	Quantum Mechanics.	
	b)	Apply the Hamilton's equations to derive the equations of motion for	
	c)	simple pendulum and linear harmonic oscillator. Write short note on	
	U)	1) Artificial Satellite	
		2) Rutherford scattering	

Seat No.			Se	et	P
M.	Sc. F	Phy	sics (Applied Electronics) (Semester - III) (New) (NEP CE Examination: March/April - 2025 Statistical Physics (2323301)	cs)
-			Thursday, 15-May-2025 Max. Ma AM To 01:30 PM	rks:	60
Instr	uctic	ns:	1) All questions are compulsory.2) Figure to the right indicate full marks.		
Q.1	A)		First and second law of thermodynamics are related by the relation a) dU=TdS-VdP b) dU=TdS+PdV c) dU=PdV-TdS d) dU=TdS-PdV		80
		2)	Helmholtz function is the amount of useful work done by a thermodynamic system at constant a) pressure b) temperature and volume c) temperature and pressure d) pressure and volume		
		3)	"At absolute zero the entropy of pure crystal is zero" is the statement of which law of thermodynamics? a) First law b) Second law c) Third law d) Fourth law		
		4)	In a grand canonical ensemble, a system A of fixed volume is in contact with a large reservoir B. Then a) A can exchange neither energy nor particles with B b) A can exchange only energy with B c) A can exchange both energy and particles with B d) A can exchange only particles with B		
		5)	In which process the pressure of the system remains constant? a) isothermal process b) isobaric process c) isometric process d) isochoric process		
		6)	In Maxwell relations, $(\partial T/\partial V)s = ?$ a) $-(\partial V/\partial S)_T$ b) $-(\partial P/\partial S)_V$ c) $(\partial S/\partial P)_T$ d) $(\partial S/\partial V)_T$		
		7)	What does occur at a critical point in critical phenomenon? a) phase transition b) symmetry breaking		

d)

scaling laws

c) universality

		8)		ectron is an example of wh			
			,	Bose Einstein statistics	b)	Maxwell Boltzmann statistics	
			c)	Fermi Dirac statistics	d)	None	
	B)	Fil	l in	the blanks OR write true	/fals	se:	04
	·	1) 2)	Du			canonical pair. (True/False) perature of a substance remains	
		3) 4)	Th	ne average K.E. of a harmo BE statistics particles have			
Q.2	Ans	swer	the	e following question (An	y Six	ς).	12
	a)		ich ¡	physical quantity remains	-	tant during the process of phase	
	b)	Wri	te o	ne example of first order p	has	e transition.	
	c)			the statistics obeyed by ph		and electron.	
				s thermodynamic potential	?		
	-			bout statistical ensemble.			
	f) g)			s phase space? s the entropy of system?			
Q.3				e following (Any Three).			12
	-			note on chemical potentia		-t	
	-			s about the thermodynami bout the condition for pha	•		
	-			note on probability calculation			
Q.4	Ans	swer	the	e following (Any Two).			12
	a)			a note of Black body radia			
	b) c)			and discuss the diagram on and explain the laws of the		oscillator in phase space. odynamics with examples.	
Q.5	Ans			e following (Any Two).			12
	a)			and discuss the Ehrenfest			
	p)			in detail about the Maxwel	_		
	c)	ΕX	plaii	n about the statistical ense	embl	es and their types.	

Seat No.						Set	Р
M.S	Sc. Ph	E	xamination	n: March/A	nester - III) (New) (NE April - 2025 Sics (2323302)	P CBCS	S)
•		Saturday, 17 AM To 01:30	•		Ма	x. Marks	: 60
Instru	ıction	s: 1) All quest 2) Figures	ions are con to the right in		narks.		
Q.1 .	•	Choose corre The singlet s a) Para-he c) Ortho-h	system of he elium	lium for S =	0 is called a positively helium ion a negatively helium ior	1	80
	2)	•	e following ca	innot be co	nserved during Raman Momentum Electronic Energy	'	
	3)	Transition of gives a) sharp s c) diffuse	eries		s s levels to lowest p le principle series fundamental series	vel	
	4)	In case of LS a) 1,2,3,4 c) 2,3,4		b)	hen J = 0,1,2,3 0,1,2,3,4		
	5)		els in atoms ses		nergy difference betwee increases zero	'n	
	6)	Atomic spec a) line spec c) band sp	ectra	mple of b) d)	continuous spectra both a and b		
	7)	a) Spin qub) Magnetc) Azimutl	ion of atomic lantum numb lic quantum r nal quantum al quantum n	er number number	pends on their		

	8)	Symmetric top molecules have	
		a) IA=IB=IC b) IA=IB≠IC	
		c) IA≠IB=IC d) IA=O, IB≠IC	
	В)	 Write true/false. 1) Splitting of spectral lines in an atom in presence electric field is called Stark effect. (True/False) 2) If Q value of nuclear reaction is positive the reaction is Exothermic. (True/False) 3) Spin angular momentum depends on s. (True/False) 4) The electronic spectra are observed in far IR region. (True/False) 	04
Q.2	a) b) c) d) e) f)	wer the following (Any Six). What are the quantum states of an electron in an atom? Define interaction energy of an atom. Write about the Paschen back effect. Define covalent interaction. What is meant by diatomic molecule? Define dissociation energy. Write about the binding energy of an atom.	12
Q.3	a) b) c)	wer the following (Any Three) Write in brief on two valence electron spectra. Discuss about origin of spectral line. State and explain Pauli's Exclusion Principle. Write a note on the vibrating diatomic molecule.	12
Q.4	a) b)	wer the following (Any Two) Write in detail about the jj coupling. Discuss about the X-ray and Auger transition. Write a note on Raman spectra.	12
Q.5	a) b)	wer the following (Any Two). What is hyperfine structure? Elaborate. Explain in detail about anharmonic oscillator. Discuss in detail about the spectrum of a non-rigid rotator.	12

Seat No.			Set	P					
M.Sc. Physics (Applied Electronics) (Semester - III) (New) (NEP CBCS) Examination: March/April - 2025 Microcontrollers & Interfacing (2323306)									
-			londay, 19-May-2025 Max. Marks: 6 M To 01:30 PM	60					
Instru	ctic	ns:	1) All questions are compulsory. 2) Figures to the right indicate full marks.						
Q.1 /	A)		On power up, the 8051 uses which RAM locations for register RO- R7	80					
			a) 00-2F b) 00-07 c) 00-7F d) 00-0F						
		2)	How many bytes of bit addressable memory is present in 8051 based microcontrollers? a) 8 bytes b) 32 bytes c) 16 bytes d) 128 bytes						
		3)	Which of the ports act as the 16 bit address lines for transferring data through it? a) PORT 0 and PORT 1 b) PORT 1 and PORT 2 c) PORT 0 and PORT 2						
		4)	Which instruction is used to check the status of a single bit? a) MOV A,P0 b) ADD A,#05H c) JNB PO.0, label d) CLR P0.05H						
		5)	Which addressing mode is used in pushing or popping any element on or from the stack? a) immediate b) direct c) indirect d) register						
		6)	Which of the following comes under the indexed addressing mode? a) MOVX A, @DPTR b) MOVC @A+DPTR,A c) MOV A,R0 d) MOV @R0,A						
		7)	If we say microcontroller is 8-bit then here 8-bit denotes size ofa) Data Bus b) ALU	Ē					

d) Address Bus

8) What is the file extension that is loaded in a microcontroller for

b)

.C

d) .hex

c) Control Bus

a) .doc

c) .txt

executing any instruction?

SLR-ZQ-16

	B)	Fill in the blank OR True/False	04
		1) Upon power-up, the I/O pins are configured as output port. True/	
		False 2) All registers of the 8051 are bit addressable. True/False	
		3) devices are specifically being used for converting serial	
		to parallel and from parallel to serial respectively.	
		4) 8051 series has16 bit registers.	
Q.2	Ans	wer the following. (Any Six)	12
	a)	What are the uses of accumulator register?	
	b)	What is mean by SFR in 8051 Microcontroller?	
	c)	What is the range of unsigned int in embedded C?	
	d)	What is the memory' size of sbit in embedded C	
	e)	What is the purpose of using instruction register?	
	f)	What is the notion for right shift in embedded C?	
	g)	What is mean by SP and PC in 8051?	
Q.3	Ans	wer the following. (Any Three)	12
• -	a)	Name the special functions registers available in 8051.	
	b)	Explain interrupt priority register of the 8051 microcontroller.	
	c)	Explain RS-232 standards.	
		•	
	d)	What are the microcontroller and what are its applications.	
Q.4	,	•	12
Q.4	,	What are the microcontroller and what are its applications.	12
Q.4	Ans a) b)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram.	12
Q.4	Ans	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED.	12
Q.4 Q.5	Ans a) b) c)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram. What are the timer and counters? Explain the operations of the same.	12
	Ans a) b) c)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram.	
	Ans a) b) c) Ans a)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram. What are the timer and counters? Explain the operations of the same. wer the following. (Any Two) Interface 16 × 2 LCD to 8051. Write a program to display "Welcome" at the centre of the first line.	
	Ans a) b) c) Ans a)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram. What are the timer and counters? Explain the operations of the same. wer the following. (Any Two) Interface 16 × 2 LCD to 8051. Write a program to display "Welcome" at the centre of the first line. Discuss Interrupt and Serial Communication.	
	Ans a) b) c) Ans a)	What are the microcontroller and what are its applications. wer the following. (Any Two) With a neat interface diagram write an embedded C code for LED. Draw 8051 architecture block diagram. What are the timer and counters? Explain the operations of the same. wer the following. (Any Two) Interface 16 × 2 LCD to 8051. Write a program to display "Welcome" at the centre of the first line.	

Seat No.							Set	P		
M.Sc. Physics (Applied Electronics) (Semester - III) (New/Old) (CBCS) Examination: March/April - 2025 Semiconductor Physics (MSC5301)										
•	Day & Date: Thursday, 15-May-2025 Time: 11:00 AM To 02:00 PM						: 80			
, .			2) Attempt a		s fron	n Q. No. 3 to Q. No. 7. arks.				
Q.1 .	A)		At 0 K the F	onential form	ution f b)	function takes the simple rectangulations the circular form	ar form	10		
		2)	a) the intrirb) the intrirc) the intrir	nsic level $ec{E_i}$ is at the	ne val r the v ne mid		,			
		3)	a) Fermi le	evel E_F	b)	ion $f(E)$ is symmetrical conduction band edge conduction band (C.E.	e Ec			
		4)	a) Smallerb) equal toc) equal to	luctor absorbs pho than band gap en the band gap ene the band gap or la the band gap or s	ergy o ergy o arger	only nly				
		5)	When trappi a) $\tau_n \neq \tau_p$ c) $\tau_n = 0$	ing is present in th	b)	terial: $ au_n = au_p \ au_p = 0$				
		6)	no barrier be that is prese a) an ohmi b) a rectifyi	etween the metal a ent is so thin that o c contact	and th charge	constructed so that the ne semiconductor, or a e carriers readily tunne ctifying	any barrier			

		If $(a + b)$ is period of potential, then for such periodic potential $V(x) = $	àl;
		a) $V[x + (a + b)]$ b) $V[x/(a + b)]$	
		c) $V[x + (a - b)]$ d) $V[x * (a + b)]$	
) is initial process that occurs in the formation of a crystal a) Growth b) Nucleation c) atomic bonding d) Clusters	al.
) In case of crystal growth process the term LPE means a) Lower Potential Energy b) Local Potential Energy c) Liquid Phase Epitaxy d) Laser phase Epitaxy	_·
	1	 In case of crystal growth process the abbreviation VPE mean a) Volume Phase Epitaxy b) Vapor Phase Epitaxy c) Variable Potential Energy d) Vapor Pressure Energy 	
	,	ill in the blank OR Write True/False The high-field excitation of electrons into the indirect minima leads to the effect.	06
) Semiconductor silicon (Si) has band gape energy; $E_g = $	_ eV.
		 Drift of charge carriers in a semiconductor is caused by The particle inside a box in a finite potential well can never be 	
		rest, as it will violate Uncertainty Principle. The inverse effective-mass tensor is a symmetric tensor of th rank.	е
) The crystal growth technique MBE means	
Q.2	Ansv	er the following question	16
	a)	Calculate the probability of an electron being thermally excited to nergy level which is $0.01~{\rm eV}$ above the Fermi level. (Given: the soltzmann constant, $k=8.625\times 10^{-5}~{\rm eV/K}$, temperature, $T=30$	
		nd value of exponent base, $e = 2.71$).	
		Discuss electrical conductivity and mobility in a semiconductor. Calculate band gap energy of a semiconductor germanium (Ge),	in
	•	lectron volt, if it absorbs a photon of wavelength 1.77 micro met low trapping of charges carries occurs in semiconductors?	
Q.3	Ansı	er the following question	16
4.0	a)	Vrite a note on "group velocity of electrons." Obtain necessary	
		xpression. Describe in detail nucleation and growth theory of crystal growth	process.
Q.4	Ansv	er the following question	16
		Discuss bonding forces in semiconductors.	
	D)	Discuss in detail formation energies of liquid nuclei and crystallin	e nuciei.

Q.5	Answer the following question				
	a)	Write a note on direct and indirect band gap materials.			
	b)	Explain how electric field is Built up by diffusion and drift of carries in the in semiconductor.			
Q.6	Ans	swer the following question	16		
	a)	Discuss in detail "The Haynes-Shockley Experiment."			
	b)	Describe dynamics of electrons and holes inside a semiconductor.			
Q.7	Ans	swer the following question	16		
	a)	Write a note on Fermi level pining.			
	b)	Explain Czochralski and liquid encapsulation techniques.			

Seat No.					Set	P
М.	Sc.	Phy	Examina	ctronics) (Sem tion: March/A lecular Physic		
-			saturday, 17-May-20 M To 02:00 PM	25	Max. Marks: 8	30
Instru	uctio	ons:	 Question No. 1 a Attempt any 3 q Figures to the right 	uestions from Q.	No.3 to Q. No. 7.	
Q.1	A)		oose correct altern Two electron specton a) Singlet and dou c) doublets and tri	ra always show _. blets b)	singlet and triplets	10
		2)	In Raman spectroso a) Microwave Reg c) UV Region	ion b)		
		3)	called	b)	in presence magnetic field is Stark effect Compton effect	
		4)	Spherical top type of a) $I_A=I_B=I_C$ c) $I_A\neq I_B=I_C$		$I_A=I_B\neq I_C$ $I_A=0,I_B\neq I_C$	
		5)	If Q value of nuclea a) Exothermic c) Endergonic		itive the reaction is Endothermic None of these	
		6)	Transition rule for that a) $\Delta \upsilon = \pm 1, \pm 2$ c) $\Delta \upsilon = \pm 1, \pm 2, \pm 3$	b)	ational spectra are Δυ = ±1 none of these	
		7)	In case of jj couplin to to form resua) its own l_i^* c) another electron	ultant j _i *. b)	etron is quantized with respect Its own s _i * another electron's s _i *	
		8)	The electronic spec a) far IR region c) visible and UV r	etra are observed b)	near IR region	

		 9) Raman effect is scattering of a) Atoms b) Molecules c) Protons d) Photons 	
	1	0) The reduced mass of a diatomic molecule as a rigid rotator is a) $(m_1+m_2)/(m_1.m_2)$ b) $(m_1.m_2)/(m_1-m_2)$ c) $m_2/(1+m_2/m_1)$ d) $m_1/(1+m_2/m_1)$	
Q.1	B)	 Fill in the blanks OR write true/false: a) The Nuclear magnetic resonance (NMR), spectrum of a molecule is observed in radio frequency range. (True/False) b) The principal quantum number determines the orientation and energy of the orbital. (True/False) c) The spectrum of radiation emitted by a black body at a temperature 1000 K peaks in the visible range of the frequencies. (True/False) d) If Q value of nuclear reaction is positive the reaction is Exothermic. (True/False) e) For l=2, ml has Possible values. f) Hyperfine structure is due to interaction of valence electrons. 	06
Q.2	a) b) c)	wer the following. Write in brief on two valence electron spectra. Write a short note on Pauli's Exclusion Principle. Explain about the Stark effect. State and discuss the Frank-Condon principle.	16
Q.3	a)		16
Q.4	Ansta)	wer the following: Obtain an expression for rotational energy level of rigid diatomic molecule. Discuss vibrational-rotational spectra in detail.	16
Q.5	Ans ^a a) b)	wer the following: Explain LS coupling scheme for two valence electron system using neat vector diagram. State and explain Lande interval rule. Represent it graphically for ³ D term.	16
Q.6	a)	wer the following: What is Zeeman effect? Distinguish between normal and anamolous Zeeman effect. What is Pachen-Back effect? Explain in detail.	16

Q.7 Answer the following:

- a) Discuss about the X-ray and Auger transition.
- b) Write an explanation of Born-Oppenheimer approximation.

Seat	Sot	D
No.	Set	

M.Sc. Physics (Applied Electronics) (Semester - III) (New/Old) (CBCS) Examination: March/April - 2025 Communication System (MSC5306)

Day & Date: Friday, 19-May-2025 Max. Marks: 80

Time: 11:00 PM To 02:00 PM

Instructions: 1) Q.Nos.1 and 2 are compulsory.

- 2) Attempt any three questions from Q.No.3 to Q.No.7.
- 3) Figure to right indicate full marks.

Q.1 A) Choose correct alternative.

- 1) Which of the following circuits is used in a Class C AM transmitter?
 - a) Push-pull amplifier
- b) Power amplifier
- c) Frequency modulator
- d) Balanced modulator
- **2)** What is the function of a VCO in an FM transmitter?
 - a) To modulate the audio signal
 - b) To generate the carrier frequency
 - c) To amplify the RF signal
 - d) To detect the frequency deviation
- **3)** Which type of modulation is used in FM radio?
 - a) Phase modulation
 - b) Amplitude modulation
 - c) Frequency modulation
 - d) Pulse modulation
- **4)** The sampling theorem states that a signal can be completely represented by its samples if the sampling rate is:
 - a) Half of the signal frequency
 - b) Equal to the signal frequency
 - c) Greater than twice the signal frequency
 - d) Equal to zero
- **5)** Which of the following is a characteristic of a balanced modulator?
 - a) It produces a double-sideband suppressed carrier signal
 - b) It amplifies the carrier frequency
 - c) It uses a single input signal
 - d) It only works with low-frequency signals
- 6) In which system is Frequency Division Multiplexing (FDM) used?
 - a) In Time Division Multiplexing
 - b) In Digital Signal Processing
 - c) In Analog Signal Transmission
 - d) In Communication Systems with multiple channels

	7)	Phase Modulation? a) ASK b) FSK c) PSK d) QAM	
	8)	The phase shift keying technique is generally used in: a) Analog systems b) Digital systems c) Audio modulation d) Video modulation	
	9)	What is the primary advantage of using TDMA in communication? a) It reduces interference b) It increases signal strength c) It allows multiple users to share the same frequency d) It minimizes signal noise	
	10)	In a Class B audio amplifier, the power output is: a) Linear b) Non-linear c) Amplified d) Distorted	
	В))6
Q.2	a) b) c) d)	xplain the block diagram of a High-Level AM transmitter. Discuss the working principle of a Class C modulated power amplifier ircuit. What are the sidebands in AM transmission? How are they formed? Describe the block diagram of an AM receiver and discuss the AM etector circuit.	6
Q.3	a) b)	rer the following: Explain the concept of FM modulation and describe the block diagram of an FM transmitter. Describe the working of a Frequency Doubler and Frequency Tripler of FM transmission systems.	6
Q.4		Wer the following What is Pulse Amplitude Modulation (PAM)? Explain its advantages and disadvantages. Discuss Delta modulation and explain its basic principle with a diagram.	6

Q.5	Ans a) b)	wer the following Discuss the role of PLL as an FM detector with a block diagram. Describe the basic operation of Frequency Shift Keying (FSK) and its applications in digital communication.	16
Q.6	a)	wer the following What are the differences between TDM and FDM? Discuss with suitable examples. Explain the working of a simple amplitude shift keying (ASK) modulator and demodulator.	16
Q.7	Ans a) b)	wer the following Describe the different transmission modes: Simplex. Half-Duplex, and Full-Duplex with examples. Explain the concept of Unipolar and Bipolar transmission and the differences between RZ and NRZ encoding schemes	16

Seat No.					Set	P		
M.So	M.Sc. Physics (Applied Electronics) (Semester - IV) (New) (NEP CBCS) Examination: March/April - 2025 Physics of Semiconductor Devices (2323401)							
•	Day & Date: Wednesday, 14-May-2025 Max. Marks: 60 Time: 03:00 PM To 05:30 PM							
Instruc	ctions		ions are compulsory to the right indicate f		arks.			
Q.1 A	() Ch	For an elect	of an energy level is	-	ability of occupancy and non- 0.5 greater than 1	80		
	2)	a) The do b) The do c) The co	ped silicon piece wi ped silicon piece wi nductivity of the dop	II bec II bec ed si	d with indium, then come n-type semiconductor come p-type semiconductor licon piece will remain the same on piece will increase)		
	3)		orbed by semicondu	ctor h	gy of the photon in joule that naving band gap of 1 eV? 1.6 x 10 ⁻¹⁹ joule 0.8 x 10 ⁻¹⁹ joule			
	4)	a) at exact b) at a less c) at a gre	of direct recombinated of the same rate as same rate as the minorice ater rate than the numble rate as the minorice.	the ity cai	rriers. ty carriers.	_•		
	5)	and a very f a) p-n jun	ast switching speed	l. b)	ith a low forward voltage drop n-p junction M-I-S			
	6)	electrons to calleda) High field	come out of its surf	ace. b)	Derature, to enable the free This type of emission is Secondary emission Thermionic emission			

	7)	Which of the following semiconductor devices converts optical energy into electrical energy? a) solar cells b) photodiodes and solar cells c) light-emitting diodes (LEDs) d) Silicon Controlled Rectifier (SCR)	
	8)	The minimum input current that can turn on a thyristor is called the a) Holding current b) Breakover current c) Trigger current d) low-current drop-out	
B)	1) 2)	Even at elevated temperature, the Fermi level lies at the middle of the band gap for intrinsic materials. (True/False) A semiconductor with a band gap of about 2 eV wide, allows only long wavelengths (infrared) and the red part of the visible spectrum to transmit through it. (True/False) In a dynamic equilibrium, there is no continual diffusion of electrons from the n to the p side (and holes from p to n). (True/False)	04
Ans a) b) c) d) e) f) g)	The pro Wh Ho Dis Wh A S cur cur	r the following question (Any Six) e probability of occupancy of an energy level is 0.6. Calculate the obability of non-occupancy of the same energy level. hat are Indirect semiconductor materials? by does the trapping of charge carriers occur in semiconductors? stinguish between drift and diffusion currents. hat is a depletion Layer? hat is Schottky barrier? Silicon solar cell has an open-circuit voltage; $V_{oc} = 0.8 \text{ V}$, a short-circuit rrent; $I_{sc} = 100 \times 10^{-3} \text{ A}$, maximum voltage; $V_m = 0.5 \text{ V}$ and maximum rrent; $I_m = 80 \times 10^{-3} \text{ A}$. Calculate the fill factor of the solar cell. If the efficiency of a solar cell	12
Ans a) b) c) d)	Wr Dis Exp Dis	r the following question (Any Three) rite a note on the effective mass of an electron/hole. scuss intrinsic and extrinsic materials. plain Optical absorption in semiconductors. scuss the Diffusion and Drift of carriers and built-in fields that occur the semiconductor.	12
Ans a) b)	Eff	r the following question (Any Two) fects of temperature and doping on mobility. scuss the Forward characteristics and reverse characteristics of the	12

Explain the principle, working, and characteristics of a light-emitting diode (LED).

Q.2

Q.3

Q.4

c)

Schottky barrier.

Q.5 Answer the following question (Any Two)a) Derive the continuity equation.b) Write a note on Gunn diode.

- c) Write a note on a Solar Cell.

Seat No.						Set	P
M.Sc. F	Phy	E	ed Electronics) kamination: Ma ear and Particle	rch/A		NEP CBC	S)
•		Friday, 16-Ma PM To 05:30	•			Max. Marks	: 60
Instructio	ns:	-	ons are compulso the right indicate	-	arks.		
Q.1 A)				of neut b) d)	rons are called isotopes isomers		08
	2)	a) 2, 8, 20,	hat contain magid 28, 50 28, 50, 82	b)	2, 8, 18, 28, 50		
	3)		-	b)	agic numbers. Fermi gas model All of these		
	4)	Two-neutron a) S_2 c) $2nS$	n separation ener	gy is d b) d)	esignated as S_{2n} S^{2n}	·	
	5)	If Q value of a) exoergic c) endoerg	;	is posi b) d)			
	6)	The inverse a) compound c) fusion	-		reaction is clipping pickup	_ reaction.	
	7)	when the ta	rget nucleus abso	orbs γ -	r more particles materay is called photoelectric effect γ – decay	<u> </u>	ed
	8)	Cyclotrons a a) negative c) neutron			elerate positive ion electron		

04

		 High binding energy means more stability of the nucleus. (True/False) Gravitational interaction is of greater strength than electromagnetic interaction. (True/False) The electric quadrupole moment is negative; shape of the nuclei is oblate. (True/False) The Rutherford scattering experiment may not be called a nuclear reaction. (True/False) 	
Q.2	a) b) c) d) e) f) g)	Write a note on composition of nucleus. Write the series of magic numbers. Why the neutron well is deeper than the proton well in nuclear potential? What is the meaning of Fermi gas in Fermi gas nuclear model? Write fission reaction upon bombarding a neutron on uranium. What is elastic and inelastic scattering? What is convenient unit of nuclear cross section and convert it into SI system? What is the name of hypothetical particle exchanged in the gravitational interaction?	12
Q.3	a) b) c)	wer the following. (Any Three) Explain meson theory of nuclear force. Give detailed account on liquid drop model. Explain the nuclear fusion with the example of the Sun. Write a note on linear accelerators.	12
Q.4	a) b) c)	wer the following. (Any Two) Explain in detail alpha, beta and gamma decay. How shell model explained the existence of all magic numbers with the help of different nuclear potentials? Give detailed account on cosmic rays and explain how geomagnetic-latitude effect on distribution of cosmic rays.	12
Q.5	Ansv		12

B) Write True/False.

Seat No.						Set	Р
M.Sc	. Physic	E	ed Electronics) xamination: Ma mmunication S	rch/	-	(NEP CB	CS)
•		esday, 20 I To 05:30	-May-2025 PM			Max. Mark	s: 60
Instruc		•	tions are compulso to the right indica	•	marks.		
Q.1 A	1)	In high-le a) Low b) Aud c) Pow	ect alternative. Evel AM, modulation power stage io stage er output stage e of the above	on oc	curs at:		08
	2)	a) Betto b) Low c) Red	er fidelity	balar	nced modulators lead	ds to	
	3)	a) Fred b) Carr c) Carr	odulation index is quency deviation to ier frequency to m ier amplitude to m e of the above	o modula	lulating frequency ation frequency		
	4)	a) Is fix	nodulation, the steed t be controlled	b)	Is variable		
	5)	a) Rad b) Sate c) Mob	onder is used in _ io broadcasting ellite communication ile towers eceivers				
	6)	a) Cons	ding is characteriz stant voltage logic	-	/ Return to zero level Bipolar pulses		

		7) PLL is mainly used ina) Power supplyb) Detectorsc) RF Amplifiersd) Filters	
		 8) Full duplex mode allows a) Two-way communication, one at a time b) One-way communication only c) Simultaneous two-way communication d) None of these 	
	B)	 Fill in the blanks OR write true/false AM bandwidth is the modulating frequency. T/F: FSK stands for Frequency Shift Keying. Modulation shifts the frequency according to signal amplitude. T/F: In simplex transmission, both sender and receiver can communicate. 	04
Q.2	a) b) c) d) e) f)	what is the filinction of an AM detector? Write two differences between high and low level modulation. Explain any two pulse modulation techniques. What are the applications of PLL? Define modulation index in FM. State any two advantages of multiplexing. Define TDMA. What is the need of modulation?	12
Q.3	a)	swer the following (Any Three) Draw and explain FM transmitter block diagram. Explain the concept of pulse code modulation. Draw and explain high level AM transmitter. Explain pulse code modulation.	12
Q.4	Ans a) b) c)	swer the following (Any Two) Explain the working of a superheterodyne receiver. Describe the principle of time division multiplexing. Compare simplex, half duplex and full duplex communication.	12
Q.5	Ans a) b) c)	Swer the following (Any Two) Describe working of ASK, FSK and PSK modulation schemes. State and prove sampling theorem. Explain generation and demodulation of PPM.	12

							,	
Seat No.							Set	P
М.	Sc.	Phy	Exam	Electronics) (S ination: March nductor Devic	ı/Ap		CBCS	5)
			Wednesday, 14-M PM To 06:00 PM	lay-2025		Max.	Marks	: 80
Instru	uctio	ons	1) Q. Nos (1) and 2) Attempt any th 3) Figures to the	rree questions f	rom	Q. No (3) to Q. No. (7)		
Q.1	A)		oose the correct In a heterojunctio a) n-type c) both (a) and	n LASER,	b)	aterials are present. p-type only n-type		10
		2)	When a vo a) breakdown c) high	oltage is applied		ne gate, the NMOS will o low both (a) and (b)	onduc	t.
		3)	•	charge carriers		removal none of these		
		4)	Flat-Band refers to voltage drop. a) little c) not defined	· ·	bnditi b) d)	ion in which there is no all of these		
		5)	When the current contact, the contact a) Rectifying c) Resistive			n both directions of the M contact. Ohmic none of these	ИS	
		6)	The point in the good begins to flow is a cut-off voltage c) threshold vo	called as ge	•	when significant current contact potential all of these		
		7)	The readout circual parallel to second parallel to par	eries	orm a b) d)	a conversion. series to parallel all of these		

		8)		ks into a pixel o			r of charge electron e time in the presence both (a) and (b)		
		9)	a) c)	reduced unchanged negative diffe theory. RWH		b) d) ance is b)	length needs to be enhanced all of these sthe concept exp		
	B)	Fill 1) 2) 3) 4) 5) 6)	NN Fe the A h the Wh cou Ph Th	e metal-semiconigher electron e energy band nen the SCR is nduction state otodiodes ope	ter than PMO ng is lowered onductor junct energy is rep diagram. (True turned from is called as _ rate after notoelectrons	S. (Tr poten ion. (7 preser le/Fals forwa bia produ	tially by the insula rue/False) ited by the higher se) rd blocking to forw asing. uced divided by th	position in vard	06
Q.2	An a) b) c) d)	Wr Dra Wr	ite ir aw a ite th	ne difference b	oncept of the diagram shov etween in de	ving c pletion	current. onstruction of Gui n and enhanceme uction of Solar Ce	ent MOSFET.	16
Q.3	An a) b)	Ela for	bora qua	ntum efficiency	acteristics of y of solar cell.		cell. Deduce an e	•	80
Q.4	An a) b)	Wh and	at a	orking of LEDs.	g diodes? Ex		he principle of co		80
Q.5	An a) b)	Wh me Exp	nat a cha plair	nism in Schottl	odes? Give th ky diode. of flat band co	nditio	ailed explanation on a condition of the detail condition.	_	08

SLR-ZQ-29

Q.6	Ans a) b)	Elaborate in detail about the basic construction and charge transfer mechanism in two phase CCD. Write in detail about LSA mode of operation.	08 08
Q.7	Ansa)	Swer the following question Give detailed explanation about the construction and working of p-n junction LASER. What are Photoconductors? Write in brief about photocurrent gain.	08

Seat No.						S	Set	P
	Sc.	Phy	E	xamination	: March/A	mester - IV) (New/Old) (Cl April - 2025 Sics (MSC5402)	BCS)
•			Friday, 16-M PM To 06:00	•		Max. M	arks:	: 80
Instr	uctio	ons:	2) Attempt	1 and 2 are co any three que to the right ind	estions fror	m Q. No. 3 to Q. No. 7.		
Q.1	A)			ements?		highest for which of the Iron Hydrogen		10
		2)	a) Quantub) Gravitac) Electron	m tunnelling		is based on which phenome	non'	?
		3)	The quark (a) uuu c) udd	composition c	of a proton b) d)	is: uud ddu		
		4)	incompress a) Shell m	sible nuclear f	luid? b)	<u> </u>		
		5)	The primar a) Electron c) Protons	ns	of cosmic b) d)	rays is: Neutrons Gamma rays		
		6)	Yukawa's t of particle? a) Electron c) Meson	•	es nuclear b) d)	r forces as mediated by whic Neutrino Photon	h typ	е
		7)	The half-life to: a) Reduce		tive substa	ance is the time taken for its	activ	ity

d)

Become constant

c) Reduce to half

		8)	a)	gic numbers are a Nuclear spin Decay constant		b)	Nuclear stability Isotopic mass	
		9)	a)	Charge conserva	ition	b)	weak interactions is: Parity conservation Baryon number conservation	
	1	10)	a) b) c)	ynchrotron is use Accelerate partic Detect cosmic ra Accelerate partic Measure binding	les in a stra ys les in a circ	aight		
	B)	 1) 2) 3) 	The cor The sta In the Co The that Alp	nversion of e shell model exploble nuclei. beta decay, a neuticle and an antino smic rays are printed binding energy per printer binding energy per per printer binding energy per per printer binding energy per	during nuclinto energy lains the co tron conver eutrino. narily comp per nucleon	clear /. ncep rts in osec dec	fusion is due to the ot of numbers for to a and emits a beta d of heavy nuclei. True/False creases for elements heavier tion power than beta particles.	06
Q.2	Ans a) b) c) d)	Exp nuc De nuc Wh me	plair clea scril clea nat is	r stability. be the liquid drop r masses. s Yukawa's hypotl s.	model and	its a	energy and its relation to applications in predicting forces? Explain the role of and its applications.	16
Q.3	Ans a) b)	Ex _l De	olair scril				applies to the nucleus. with an emphasis on the	16
Q.4	Ans a) b)	De Dis	rive scus	•			lear resonance reactions. he concept of quantum	16

16

	b)	What are cosmic rays? Discuss their origin and effects on the Earth's atmosphere.	
Q.6	Ans	wer the following.	16
	a)	Explain nuclear fission and fusion with suitable examples.	
	b)	Describe the functioning of a cyclotron and its application in nuclear physics.	
Q.7	Ans	wer the following	16
	a)	Discuss the conservation laws in nuclear reactions with examples.	
	b)	Explain the working principle of scintillation detectors and their applications.	

Classify elementary particles based on their interactions. Explain with

Q.5 Answer the following.

examples.

Seat No.		Set	Р
M.Sc	. Physics (Appl	ied Electronics) (Semester - IV) (New/Old) (CBC	CS)

W.SC. Physi	Examination: Marc Microwave Devices & 0	ch/	•
Day & Date: Tu Time: 3:00P.M.	uesday 20 May 2025 .To 6:00PM		Max. Marks: 80
2	1) Q.1 and Q .2 are compulsor 2) Attempt any three questions 3) Figure to the right indicate f	s fro	
-	oose correct alternatives (MC	CQ)	10
1)	Reflex klystron is a a) Low power generator c) Low gain amplifier		
2)	Microwaves travel in a a) Distorted line c) Straight lines		
3)		t se	nds energy from one location
	to another. a) Transmission line c) Fibre cable lines	-	
4)	types of transmission a) 3	line b)	
	c) 4	d)	
5)	a) TWT c) Magnetron	b)	rith a cross field Theory. Reflex Klystron Double cavity klystron
6)	is the standard form of a) Travelling White Tube b) Travelling Wave Tube c) Travelling Wave Tire d) Travelling Weight Tube	of T	WT.
7)	The gain bandwidth product decibels. a) <10dB c) > 200 dB	of (b) d)	Gunn diode is around >10dB infinite dB

		8)	a)	TEM		b)		
		9)	C)	TE		•	TE, TM tron amplifier is a type	
		3)		am amplifier.	useu III a k	ıyə	tron ampliner is a type	
			a)	Linear beam		,	Crossed field	
			C)	Parallel field		u)	None of the	
		10)		is not Micro			Transistar	
			,	IC LED		,	Transistor Varacter diode	
	B)			e blanks OR v				06
		1)	bar	•	ige iroin o	.0	12 GHz is designated as X	
		2)	-	stron amplifiers	-	no	ise output as compared to	
		3)		e structure of G		has	s 3 layers.	
		4)		•	nge from 4 t	to 8	3 GHz is designated as L	
		5)	bar A K	ia. (lystron amplifi	er device u	ses	a helix.	
		6)	Lar	ge size is the a	advantages	of	Gunn diode.	
Q.2				following.			5 (1 1 (1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	16
	a)			about the diffei Klystron.	ences betw	/ee	n a Reflex Klystron and two	
		Desc	cribe	Ridley- Watkii				
	-	-		n short the Ma short note on co		atic	ons.	
Q.3	Λne	swar f	tha f	following				
Q.J		Desc	cribe	the Various m			tion of Reflex klystron	10
	b)	Disco band		how the microv	vave spectr	um	n is categorized into different	06
Q.4	Ans	swer t	he f	following.				
	a)			help of velocity amplifier.	/ diagram e	xpl	ain principle of two-cavity	10
	b)	•		wn the various	Microwave	ар	pplications.	06
Q.5	Ans	swer t	he f	ollowing.				
	a) b)			Gunn Effect? E ort notes on wa		n d	liode in detail	10 06
	•							

Q.6		Explain the possibility of oscillations in a TWT amplifier. Derive the expressions for the field components due to TM waves in rectangular wave guide.	80 80
Q.7	Ans	swer the following	
	a)	Why TEM modes are not possible in hollow rectangular waveguide? Prove it.	80
	b)	For a wave guide having cross section 3cm x 2cm, compute the cut-off frequency in the TE01 mode. Also, calculate the phase velocity and guide wavelength at a frequency equal to 50% above the cut-off frequency	08

Seat	Set	D
No.	Set	Г

M.Sc. PHYSICS (APPLIED ELECTRONICS) (Semester - IV) (New/Old) (CBCS) Examination: March/April - 2025 Microcontrollers & Interfacing (MSC5406)

	Microcontrollers & II	ILCII	acing (WSC3400)	
•	Thursday, 22-May-2025 PM To 06:00 PM			Max. Marks: 80
Instructions	s: 1) Q.Nos 1 and 2 are computed: 2) Attempt any three from Q 3) Figure to the right indicate	. No.	3 to Q. No. 7.	
1) a)	lultiple choice questions: The internal ROM memory of t) 8K) 256K	he 80 b) d)	051 is 128K 4K	10
a)	The 8051 has 16-bit regi:) 1) 3	sters b) d)	2 4	
a)	The 8051 can handle bit) 8) 2	data b) d)	at the same time. 4 6	
a)	The 8051 IC can be available i) 40) 30	in b) d)	pin DIP package. 28 20	
a)	The D7 bit in PSW from D0-D7) Carry) Parity	7 is _ b) d)	flag. Zero Overflow	
	used to select the registe) PC) SP	er bar b) d)	nks in 8051. RS0-RS1 ALU	
7) a) c)) MOV A #35H		ue 35H immediate in t MOV A, 35H MOV #35H, A	he accumulator.
	When 8051 wakes up then 0x0) SP) DPTR	00 is b) d)	loaded to registe PC PSW	er.

	9)	a) 000 to FFFH b) 00 to FFH c) 0000 to FFFFH d) 0 to FH	ess range of.	
	10)	 The bits of the register PSW affected if we select a) PSW.5 =0 and PSW.4 =1 b) PSW.2 =0 ar c) PSW.3 =1 and PSW.4 =1 d) PSW.3 =0 ar 	nd PSW.3 =1	_•
		 State true or false: PSW register is 8 bits wide in size. 8051 series microcontroller family has six regist 8051 microcontrollers has 8 bits unidirectional of On power up, the 8051 uses 00-07 RAM location R7. 16 bytes of bit addressable memory is present in microcontrollers. Auxiliary carry is set when carry is generated from 	er banks. lata bus. ns for register R0- n 8051 based	06
Q.2	a) b) c)	swer the following: Write a short note on TCON SFR for 8051 Microco Describe SCON register for serial communication. Explain oscillator and clock of 8051 microcontrolle What is common anode and common cathode 7-s	ontroller. r.	16
Q.3	Ans a) b)	eswer the following: Explain how to interface push button with 8051 mi C program. Explain different modes of Timer for 8051 microco)8)8
0.4	•	·		. •
Q.4	a) b)	, ,		10)6
Q.5	Ans a) b)	Describe each block in detail.		10 06
Q.6	Ans	swer the following:		
-	a)	Draw 40- pin diagram of 8051 microcontroller. Expeach pin in detail.	plain the function of 1	0
	b)	Explain how to interface LED with 8051 microcont program.	rollers with C)6

Q.7	Answer the following:					
	a)	Describe the data transfer instructions and arithmetic instructions of 8051 microcontroller with examples.	10			
	b)	Explain the port programming in 8051 microcontrollers.	06			